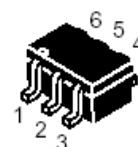


Silicon PNP Epitaxial Planer Transistor

L4401DW1T1



SC88

MAXIMUM RATINGS

Parameter	Symbol	Ratings	Unit
Collector-Emitter Voltage	V_{CEO}	-50	V
Collector-Base Voltage	V_{CBO}	-60	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector current-continuoun	I_C	-150	mAdc

THERMAL CHARATEERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1) $T_A=25^{\circ}\text{C}$	P_D	380	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	328	$^{\circ}\text{C/W}$
Junction and Storage Temperature	T_j, T_{stg}	-55 to +150	$^{\circ}\text{C}$

DEVICE MARKING

L4401DW1T1=5K

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C=-1\text{mA}$)	$V_{(BR)CEO}$	-50	-	-	V
Emitter-Base Breakdown Voltage ($I_E=-50\mu\text{A}$)	$V_{(BR)EBO}$	-6	-	-	V
Collector-Base Breakdown Voltage ($I_C=-50\mu\text{A}$)	$V_{(BR)CBO}$	-60	-	-	V

Collector Cutoff Current ($V_{CB}=-60V$)	ICBO	-	-	-0.1	μA
Emitter Cutoff Current ($V_{BE}=-6V$)	IEBO			-0.1	μA

ON CHARACTERISTICS

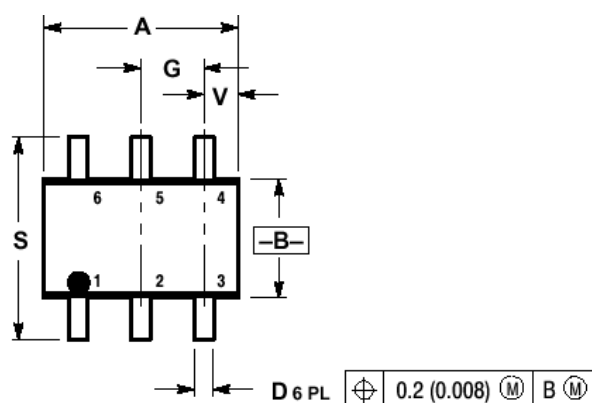
DC Current Gain ($I_C=-1mA$, $V_{CE}=-6.0V$)	Hfe	120	-	560	
Collector-Emitter Saturation Voltage ($I_C=-50mA$, $I_B=-5mA$)	VCE(SAT)	-	-	-0.5	V

SMALL-SIGNAL CHARACTERISTICS

Current-Gain-Bandwidth Product ($V_{CE} = -12.0V$; $I_E = 2.0 mA$, $f=300MHz$)	Ft	-	140	-	MHz
Output Capacitance($V_{CB}=-12V$, $f=1.0MHz$)	Cobo	-	4	5	Pf

PACKAGE DIMENSIONS

SC-88



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	—	0.004	—	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20
V	0.012	0.016	0.30	0.40